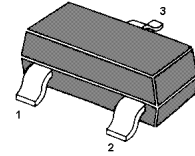


MMBTSA1162

PNP Silicon Epitaxial Planar Transistor

for AF general purpose amplifier applications.

The transistor is subdivided into three groups O, Y and G, according to its DC current gain.



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{\text{CBO}}$	50	V
Collector Emitter Voltage	$-V_{\text{CEO}}$	50	V
Emitter Base Voltage	$-V_{\text{EBO}}$	5	V
Collector Current	$-I_{\text{C}}$	150	mA
Base Current	$-I_{\text{B}}$	30	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_{J}	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{\text{CE}} = 6\text{ V}$, $-I_{\text{C}} = 2\text{ mA}$	Current Gain Group O Y G h_{FE} h_{FE} h_{FE}	70	140	-
		120	240	-
		200	400	-
Collector Base Cutoff Current at $-V_{\text{CB}} = 50\text{ V}$	$-I_{\text{CBO}}$	-	0.1	μA
Emitter Base Cutoff Current at $-V_{\text{EB}} = 5\text{ V}$	$-I_{\text{EBO}}$	-	0.1	μA
Collector Base Breakdown Voltage at $-I_{\text{C}} = 100\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{CBO}}$	50	-	V
Collector Emitter Breakdown Voltage at $-I_{\text{C}} = 10\text{ mA}$	$-V_{(\text{BR})\text{CEO}}$	50	-	V
Emitter Base Breakdown Voltage at $-I_{\text{E}} = 10\text{ }\mu\text{A}$	$-V_{(\text{BR})\text{EBO}}$	5	-	V
Collector Emitter Saturation Voltage at $-I_{\text{C}} = 100\text{ mA}$, $-I_{\text{B}} = 10\text{ mA}$	$-V_{\text{CE(sat)}}$	-	0.3	V
Gain Bandwidth Product at $-V_{\text{CE}} = 10\text{ V}$, $-I_{\text{C}} = 1\text{ mA}$	f_{T}	80	-	MHz
Collector Output Capacitance at $-V_{\text{CB}} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	7	pF

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